IGBT Ignition Predriver with Dynamic Current Regulation

The CS8312 is a bipolar microprocessor interface IC designed to drive an IGBT (or logic level MOSFETs) powering large inductive loads in harsh operating environments. The IC's dynamic current limit function lets the microprocessor adjust the current limit threshold to the real time needs of the system.

CLI, the current limit input, sets the current limit for the IGBT high or low as directed by the system microprocessor. CLI also raises and lowers the threshold on the diagnostic FLAG output signal. The FLAG output signals the microprocessor when the current level approaches current limit on the IGBT. The CTRL input enables the FLAG function.

Features

- µP Compatible Inputs
- Adjustable Current Limit Thresholds
- External Sense Resistor
- Flag Signal to Indicate Output Status

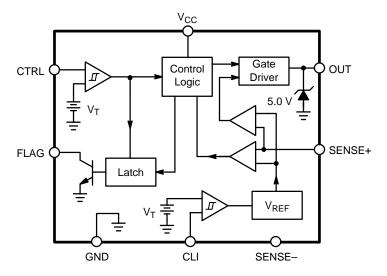
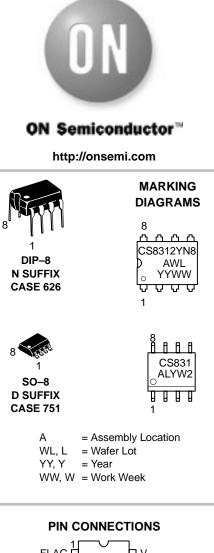
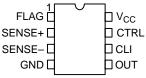


Figure 1. Block Diagram





ORDERING INFORMATION

Device	Package	Shipping
CS8312YN8	DIP-8	50 Units/Rail
CS8312YD8	SO-8	95 Units/Rail
CS8312YDR8	SO–8	2500 Tape & Reel

ABSOLUTE MAXIMUM RATINGS*

Ra	ting	Value	Unit
Supply Voltage		-0.3 to 12	V
Digital Input Currents		2.0	mA
Internal Power Dissipation ($T_A = 25^{\circ}C$)	Internal Power Dissipation ($T_A = 25^{\circ}C$)		mW
Junction Temperature Range	-40 to +150	°C	
Storage Temperature Range	-55 to +165	°C	
Electrostatic Discharge (Human Body Model)	2.0	kV	
Lead Temperature Soldering	Wave Solder (through hole styles only) Note 1. Reflow (SMD styles only) Note 2.	260 peak 230 peak	°C O°

1. 10 seconds max.

2. 60 seconds max above $183^{\circ}C$

*The maximum package power dissipation must be observed.

$\label{eq:constraint} \begin{array}{l} \textbf{ELECTRICAL CHARACTERISTICS} & (7.0 \ V \leq V_{CC} \leq 10 \ V, -40^{\circ}C \leq T_A \leq 125^{\circ}C, \\ -0.2 \ V \leq \text{Differential Ground Voltage} \leq 0.8 \ V; \ \text{unless otherwise specified.}) \end{array}$

Characteristic **Test Conditions** Min Тур Max Unit General 7.0 V Power Supply Including Ripple Voltage 10 _ _ Supply Ripple Frequency _ 10 _ 60 kHz kHz **Differential Ground Frequency** _ 10 _ 60 Quiescent Current, IQ Turn On $V_{CTRL} = 5.5 V$ 15 mΑ _ _ Turn Off $V_{CTRL} = -0.3 V$ 5.0 mΑ _ _ $V_{CTRL} = 5.5 V$ 30 dB Supply Voltage Rejection _ _ **Differential Ground Rejection Ratio** $V_{CTRL} = 5.5 V$ 30 _ _ dB **Differential Ground Current Ratio** $V_{CTRL} = -0.3 V,$ 3.0 mΑ $(V_{SENSE-} - V_{GND})DC = 1.0 V$ $(V_{SENSE-} - V_{GND})AC = 0.6 V$ Unity Gain Bandwidth $V_{CTRL} = 5.5 V$ 400 _ _ kHz **CTRL** Increasing Turn On Delay _ _ 30 μs Turn Off Delay 30 **CTRL** Decreasing _ _ μs **Control Function** Input Voltage Range $I_{CTRL} = 2.0 \text{ mA}$ -0.3 5.5 V _ Input Threshold Turn On **CTRL** Increasing 3.5 V Turn Off **CTRL** Decreasing 1.5 V _ Hysteresis 2.0 V 0.4 _ _ Voltage $I_{CTRL} = 10 \ \mu A \ max$ _ 1.1 V Input Capacitance _ _ _ 50 pF **Current Limit Increase Function** Input Voltage Range V $I_{CTRL} = 2.0 \text{ mA}$ -0.3 _ 5.5 Input Threshold Turn On **CLI** Increasing V 3.5 Turn Off **CLI** Decreasing 1.5 V Hysteresis 0.4 _ 2.0 V V Voltage $I_{CLI} = 10 \ \mu A \ max$ _ _ 1.1

CS8312

ELECTRICAL CHARACTERISTICS (continued) (7.0 V \leq V_{CC} \leq 10 V, -40°C \leq T_A \leq 125°C,

 $-0.2 \text{ V} \leq \text{Differential Ground Voltage} \leq 0.8 \text{ V}$; unless otherwise specified.)

Characteristic	Test Conditions	Min	Тур	Max	Unit
Current Limit Increase Function (co	ontinued)	·			
Input Capacitance	-	-	-	50	pF
Output Stage					
I _{OUT}	_	-	-	5.0	mA
Clamp Voltage	V _{CTRL} = 5.5 V, I _{OUT} = 1.0 mA	4.0	-	5.5	V
Output Off Voltage	$V_{CTRL} = -0.3 \text{ V}, I_{OUT} = 10 \mu\text{A}$ $V_{CTRL} = -0.3 \text{ V}, I_{OUT} = 200 \mu\text{A}$			0.5 1.2	V V
Flag Function		·			
Output Low	V_{CTRL} = 5.5 V, I_{FLAG} = 1.5 mA	-	-	0.9	V
Leakage Current	V _{CTRL} = -0.3 V	-	-	10	μΑ
Output Capacitance	-	-	-	50	pF
Turn On (V _{SENSE+} – V _{SENSE} –)	$V_{CTRL} = 5.5 V, V_{CLI} = -0.3 V$ $V_{CTRL} = 5.5 V, V_{CLI} = 5.5 V$	210 300	225 -	240 350	mV mV
Turn Off Delay	CTRL Decreasing	-	-	10	μs
Turn On Delay	_	-	-	10	μs
Disable Time	-	100	-	450	μs
Sense Function		·			
Input Voltage Range	-	-0.3	-	2.5	V
Sense Regulation Voltage	$V_{CTRL} = 5.5 V, V_{CLI} = -0.3 V$ $V_{CTRL} = 5.5 V, V_{CLI} = 5.5 V$	270 380	295 410	320 440	mV mV
Input Leakage Current	V _{CTRL} = 5.5 V	-	-	5.0	μΑ
Propagation Delay	V _{CTRL} = 5.5 V	-	-	20	μs

PACKAGE PIN DESCRIPTION

PACKAGE PIN #				
DIP-8	SO–8	PIN SYMBOL	FUNCTION	
1	1	FLAG	Indicates whether current through the IGBT has reached a pre- set level.	
2	2	SENSE+	Positive input to current comparator.	
3	3	SENSE-	Ground (SENSE-) for current sense resistor.	
4	4	GND	Ground connection.	
5	5	OUT	Output voltage to IGBT (MOSFET) gate.	
6	6	CLI	Current limit input increase.	
7	7	CTRL	Control input.	
8	8	V _{CC}	Supply voltage.	

CS8312

CIRCUIT DESCRIPTION

Flag Function (See Figure 2)

The flag indicates when the voltage across the two sense pins is approaching a current limit level that has been determined by the value of the external sense resistor (R_{SENSE}) and the state of the CTRL and CLI pins. If the voltage across the sense pins (SENSE+, SENSE–) is less than the flag turn–on voltage, then the FLAG is off. When the voltage between the sense pins equals the FLAG turn on voltage, the FLAG will latch on until the CTRL pin goes low. FLAG is disabled whenever CTRL is low. Changing the CLI pin from low to high will increase nominal FLAG turn on voltage by approximately 45%.

	-		
State	CONTROL	SENSE+	FLAG
0	Low	Х	OFF
1	High	Below Threshold	OFF
2	High	Above Threshold	ON
3	High	Х	ON
0	Low	Х	OFF

Table 1. FLAG Timing Sequence

Output Stage

The CS8312 output (OUT) saturates and supplies voltage to the IGBT (or MOSFET) gate once the CTRL switches from low to high. As current through the IGBT (MOSFET) increases and the voltage across the sense resistor passes the flag turn on voltage, the FLAG will turn on. If the current through the sense resistor continues to rise and the sense resistor voltage reaches the regulation sense voltage, then the gate voltage will fall to a level that regulates the driver and maintains the regulation sense voltage at the sense resistor.

Current Limit Function

Changing the CLI pin from a logic low to a logic high increases the FLAG turn on voltage by approximately 45% and the regulation sense voltage by approximately 39% respectively.

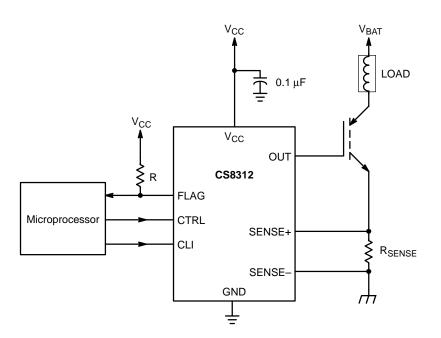
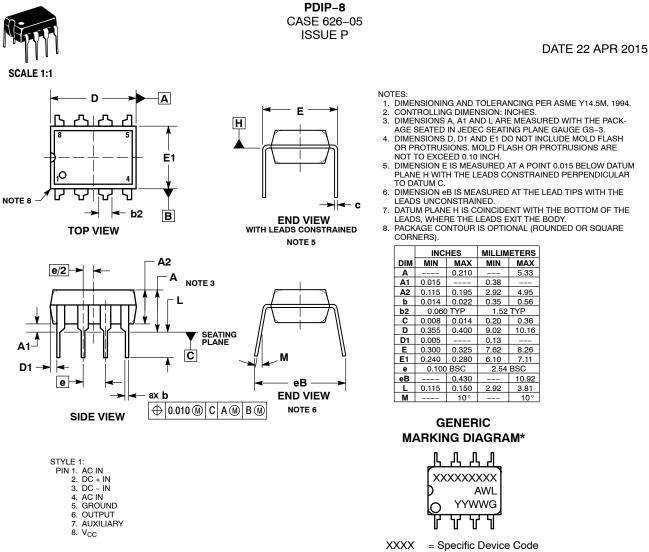


Figure 2. Application and Test Diagram

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A = Assembly Location

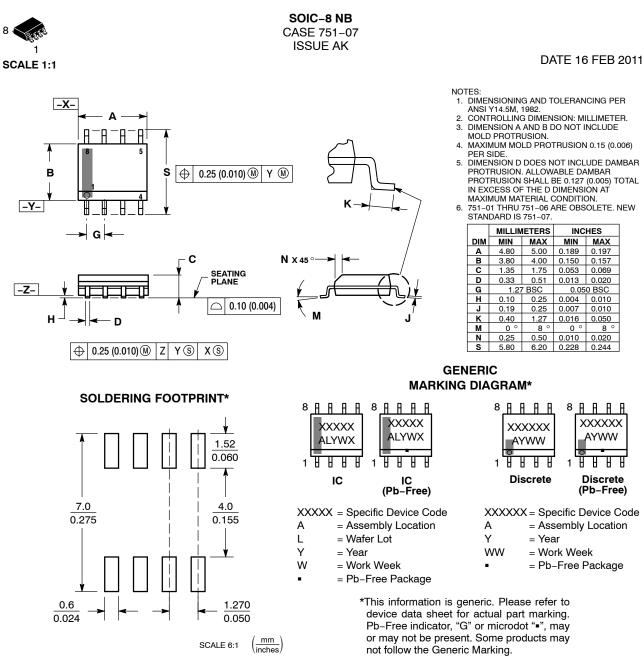
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR 3. 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT 6. IOUT IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE

6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK

7. VOULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

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COLLECTOR, #1

COLLECTOR, #1

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